



INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)			ATTY DOCKET NO.	SERIAL NO.			
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			APPLICANT(S): YING ZHOU, ET AL.				
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U.S. PATENT DOCUMENTS							
*EXAMINE R INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.							
B.							
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
J.							
K.							
L.							
M.							
N.							
O.							
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>ML</i>	P.	Robert M. Wallace, "Challenges for the Characterization and Integration of High-k Gate Dielectrics," pp. 1-50, Nov. 2002, http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf					
<i>ML</i>	Q.	Gerry Lucovsky, "The Physics and Chemistry of High-k Dielectrics and their Interfaces," pp. 1-49, available on June 2003, at http://www.sematech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf					
	R.						
	S.						
	T.						
EXAMINER <i>Michelle Ortada</i>				DATE CONSIDERED	<i>9/27/04</i>		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.